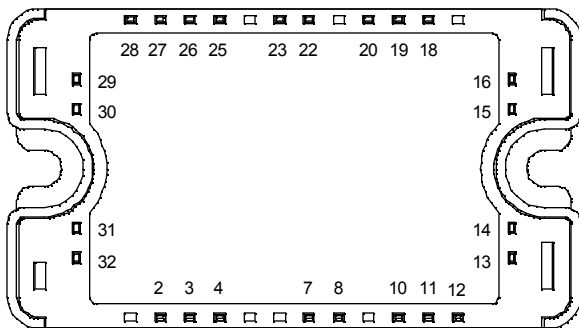
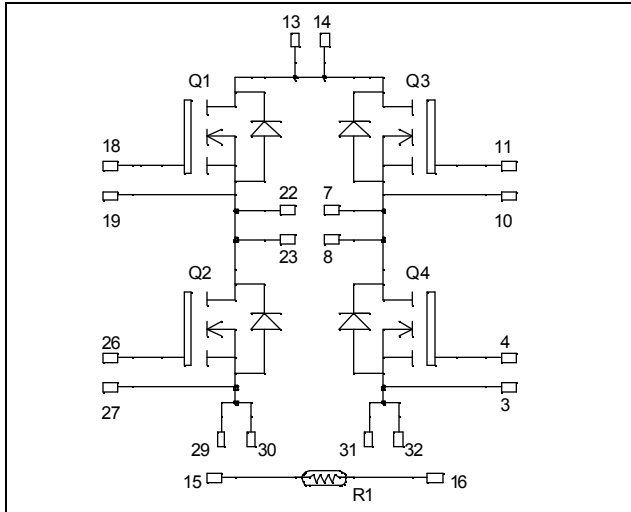


## Full - Bridge Super Junction MOSFET Power Module

$V_{DSS} = 800V$   
 $R_{DSon} = 150m\Omega \text{ max @ } T_j = 25^\circ C$   
 $I_D = 28A \text{ @ } T_c = 25^\circ C$



All multiple inputs and outputs must be shorted together  
 Example: 13/14 ; 29/30 ; 22/23 ...

### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

### Features

- **COOLMOS** Power Semiconductors
  - Ultra low  $R_{DSon}$
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	800	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	28
		$T_c = 80^\circ C$	21
$I_{DM}$	Pulsed Drain current	110	
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	150	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	277
$I_{AR}$	Avalanche current (repetitive and non repetitive)	17	A
$E_{AR}$	Repetitive Avalanche Energy	0.5	mJ
$E_{AS}$	Single Pulse Avalanche Energy	670	

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}, V_{DS} = 800\text{V}$			50	$\mu\text{A}$
		$T_j = 25^\circ\text{C}$				
		$V_{GS} = 0\text{V}, V_{DS} = 800\text{V}$			375	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 14\text{A}$			150	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2\text{mA}$	2.1	3	3.9	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			$\pm 150$	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}$		4507		pF
$C_{oss}$	Output Capacitance	$V_{DS} = 25\text{V}$		2092		
$C_{rss}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		108		
$Q_g$	Total gate Charge	$V_{GS} = 10\text{V}$		180		nC
$Q_{gs}$	Gate – Source Charge	$V_{Bus} = 400\text{V}$		22		
$Q_{gd}$	Gate – Drain Charge	$I_D = 28\text{A}$		90		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive switching @ <math>125^\circ\text{C}</math></b>		10		ns
$T_r$	Rise Time	$V_{GS} = 15\text{V}$		13		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 533\text{V}$		83		
$T_f$	Fall Time	$I_D = 28\text{A}$		35		
		$R_G = 2.5\Omega$				
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>25^\circ\text{C}</math></b>		486		$\mu\text{J}$
$E_{off}$	Turn-off Switching Energy	$V_{GS} = 15\text{V}, V_{Bus} = 533\text{V}$		278		
		$I_D = 28\text{A}, R_G = 2.5\Omega$				
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>125^\circ\text{C}</math></b>		850		$\mu\text{J}$
$E_{off}$	Turn-off Switching Energy	$V_{GS} = 15\text{V}, V_{Bus} = 533\text{V}$		342		
		$I_D = 28\text{A}, R_G = 2.5\Omega$				

**Source - Drain diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_S$	Continuous Source current (Body diode)	$T_c = 25^\circ\text{C}$		28		A
		$T_c = 80^\circ\text{C}$		21		
$V_{SD}$	Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -28\text{A}$			1.2	V
$dv/dt$	Peak Diode Recovery ❶				6	V/ns
$t_{rr}$	Reverse Recovery Time	$I_S = -28\text{A}$		550		ns
		$V_R = 400\text{V}$				
$Q_{rr}$	Reverse Recovery Charge	$di_S/dt = 200\text{A}/\mu\text{s}$		30		$\mu\text{C}$
		$T_j = 25^\circ\text{C}$				

 ❶  $dv/dt$  numbers reflect the limitations of the circuit rather than the device itself.

 $I_S \leq -28\text{A}$     $di/dt \leq 200\text{A}/\mu\text{s}$     $V_R \leq V_{DSS}$     $T_j \leq 150^\circ\text{C}$

## Thermal and package characteristics

### Symbol Characteristic

Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance			0.45	°C/W	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, I <sub>isol</sub> <1mA, 50/60Hz	2500			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				110	g

## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

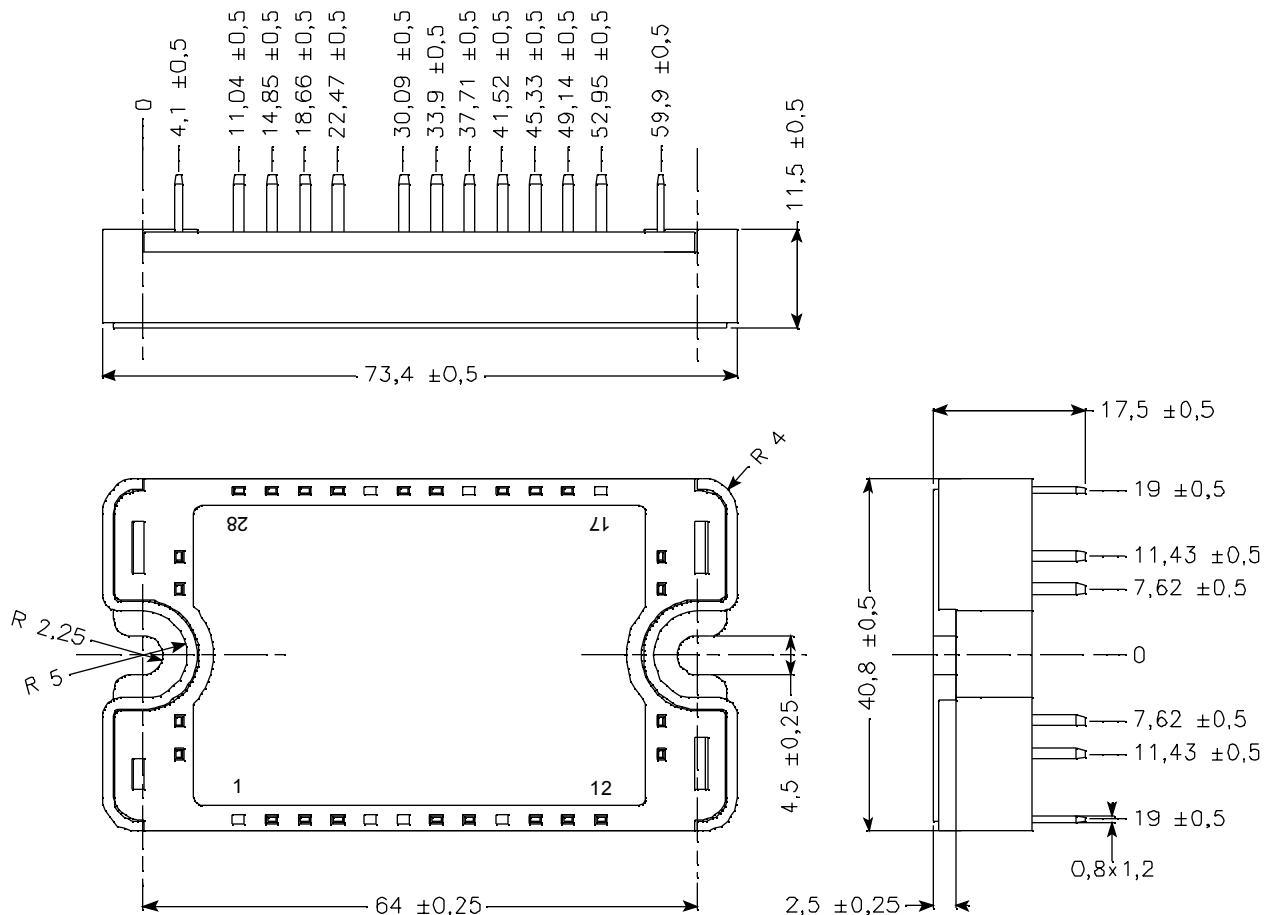
### Symbol Characteristic

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

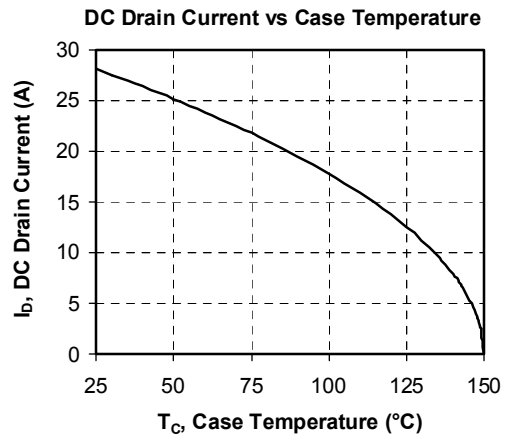
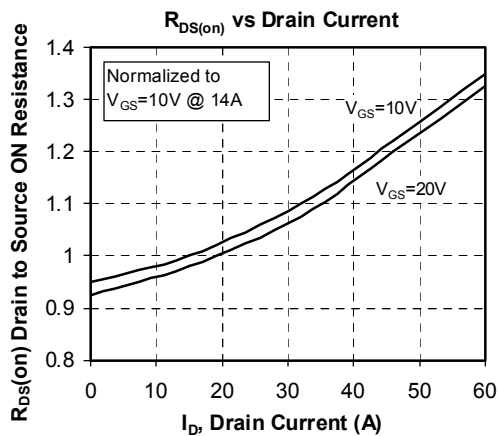
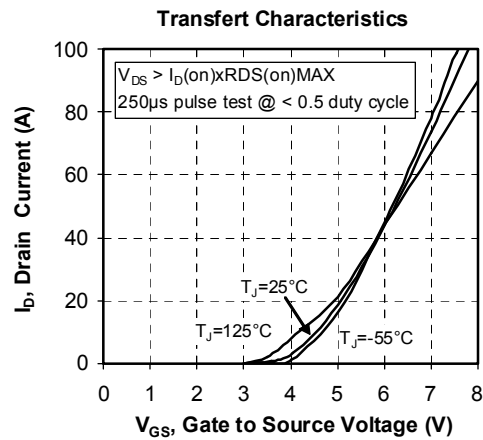
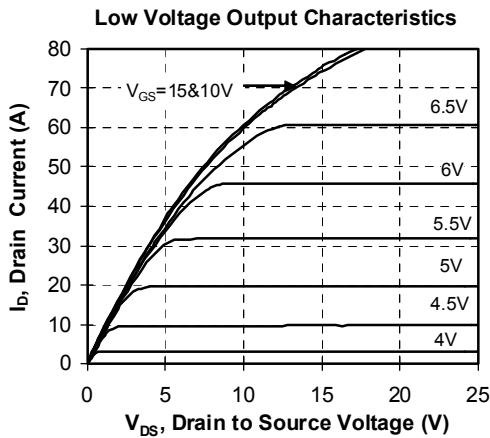
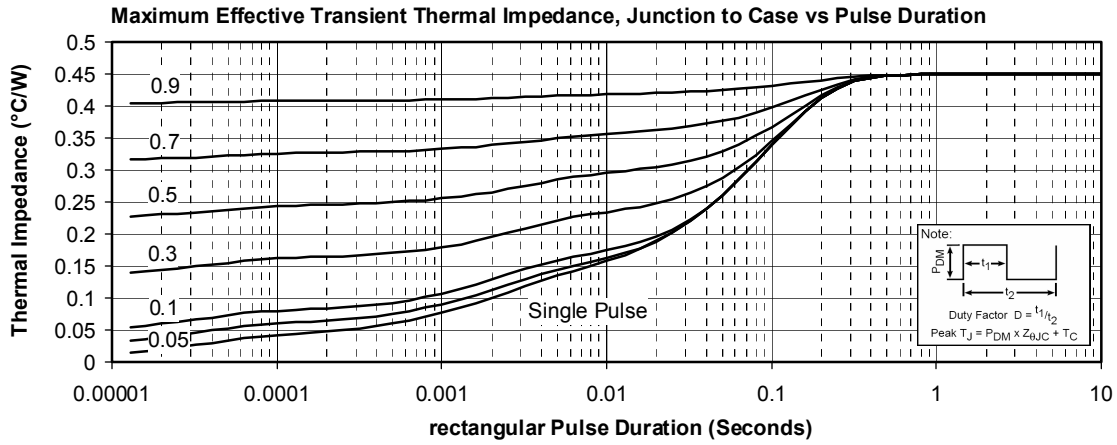
T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

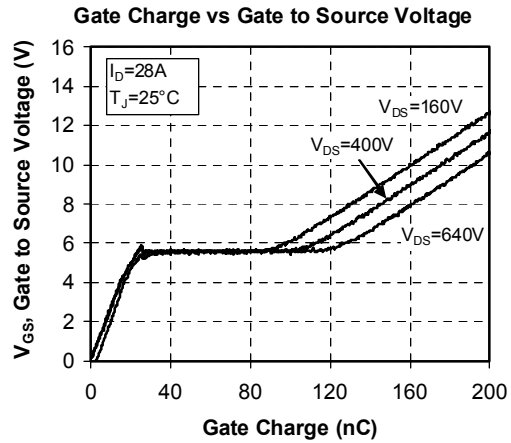
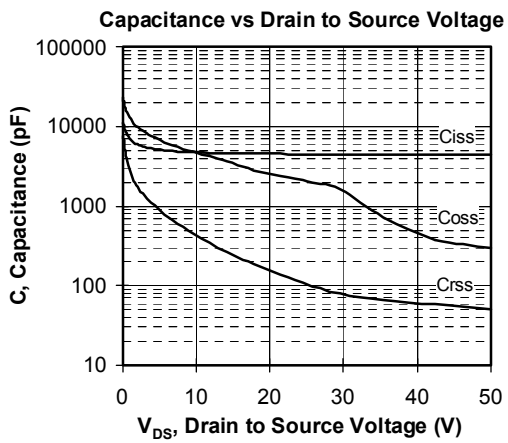
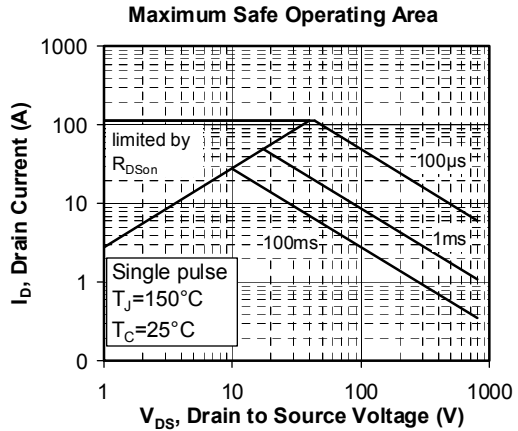
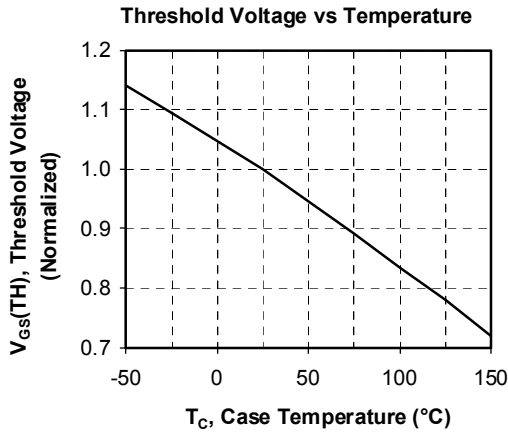
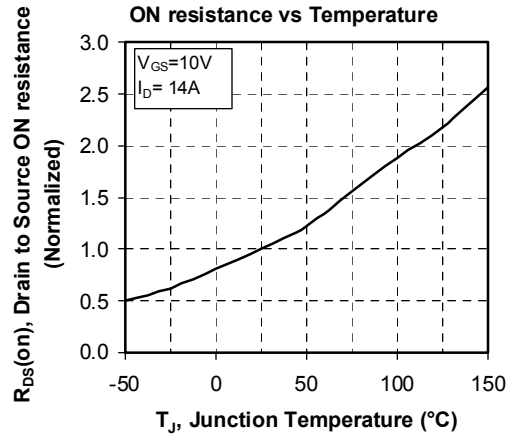
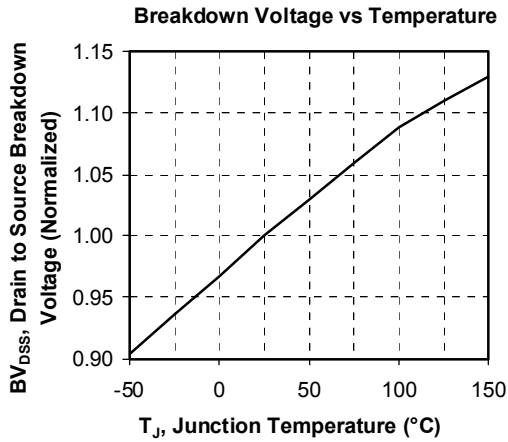
## SP3 Package outline (dimensions in mm)

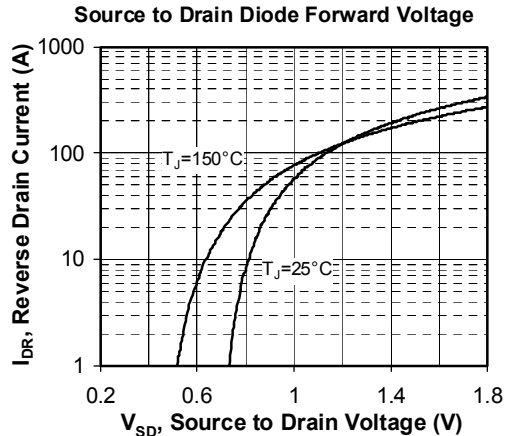
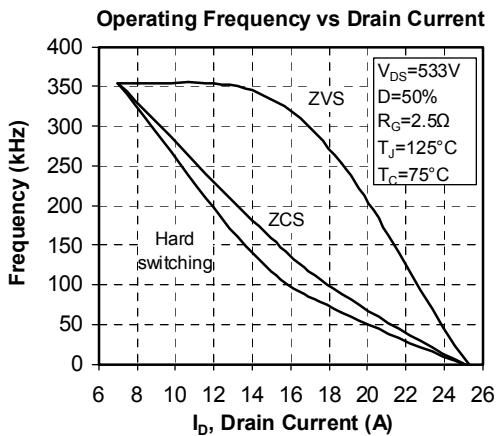
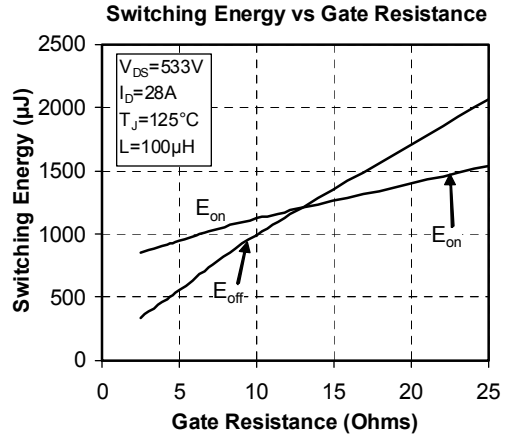
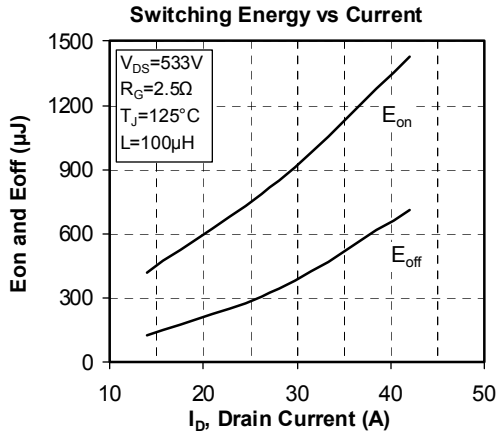
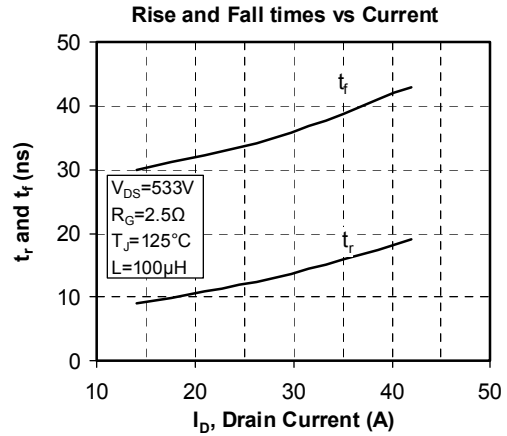
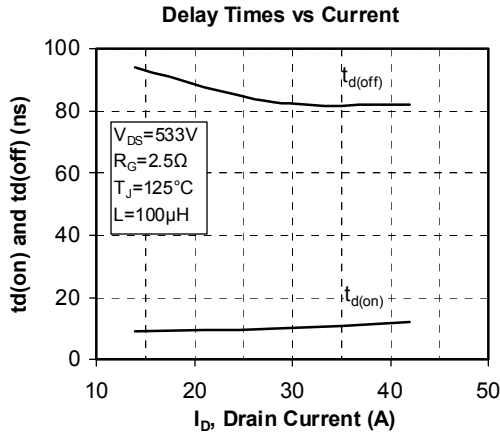


See application note 1901 - Mounting Instructions for SP3 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve







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